L Nu	mber	Hits	Search Text	DB	Time stamp
1		2	5888857.pn.	USPAT;	2003/08/08 10:55
		_	÷	US-PGPUB;	
				EPO; JPO;	
				DERWENT;	
			·	IBM_TDB	
2		2	5744822.pn.	USPAT;	2003/08/08 10:55
				US-PGPUB;	
				EPO; JPO;	
				DERWENT;	•
_				IBM_TDB	
3		16	(US-6346437-\$ or US-6319761-\$ or	USPAT;	2003/08/08 11:44
			US-6162667-\$ or US-5804473-\$ or US-5252502-\$	US-PGPUB	
			or US-5147826-\$ or US-6084247-\$ or		
			US-6077731-\$ or US-5275851-\$ or US-6475840-\$		
			or US-5932893-\$ or US-5580792-\$ or US-6413805-\$ or US-5744822-\$ or		
			US-5624851-\$).did. or		
	,		(US-20010053613-\$).did.	,	
4		51	("4727044"   "5147826"   "5200846"	USPAT	2003/08/08 11:47
1		]	"5275851"   "5313076"   "5318661"	OSFAI	2003/08/08 11.47
		· ·	"5352291"		
			"5481121"		
			"5501989"   "5508533"   "5529937"		
	.		"5531182"   "5534716"   "5543352"		
1			"5563426"   "5569610"   "5569936"		
		,	"5580792" "5585291" "5589694"		
		•	"5595923"   "5595944"   "5604360"		
			"5605846"   "5606179"   "5608232"		
			"5612250"   "5614426"   "5614733"		
			"5616506"   "5620910"   "5621224"		
			"5624851"   "5637515"   "5639698"		•
			"5643826"   "5646424"   "5654203"		
			"5656825"   "5663077"   "5677549"		
			"5696386"   "5696388"   "5700333"	•	·
	-		"5705829"   "5712191"   "5756364").PN.		
-		430	(tft or thin adj film adj transistor) and	USPAT;	2003/08/06 15:44
4.			(single adj grain or single adj crystal or	US-PGPUB;	
			polycrystal or single adj crystalline or	EPO; JPO;	
			polycrystalline or poly adj crystal or poly adj crystalline or polysilicon or large adj	DERWENT;	
			grain) with (doping or dopant or doped or	IBM_TDB	
			implant or implanting or implantation or		
			implanted or diffusing or diffusion or		
			diffused) with (aluminum or al or nickel or		
			ni or titanium or ti or cobalt or co or		
	-		palladium or pd or transition adj metal)	-	
-		282	((tft or thin adj film adj transistor) and	USPAT;	2003/08/06 15:10
	. !		(single adj grain or single adj crystal or	US-PGPUB;	
			polycrystal or single adj crystalline or	EPO; JPO;	
	l		polycrystalline or poly adj crystal or poly	DERWENT;	
			adj crystalline or polysilicon or large adj	IBM TDB	
			grain) with (doping or dopant or doped or	_	
			implant or implanting or implantation or		
			implanted or diffusing or diffusion or		
			diffused) with (aluminum or al or nickel or		
			ni or titanium or ti or cobalt or co or		
			palladium or pd or transition adj metal))		,
1			and (anneal or annealing or annealed)		
		188	(tft or thin adj film adj transistor) and	USPAT;	2003/08/06 15:45
			(single adj grain or single adj crystal or	US-PGPUB;	
ļ.			polycrystal or single adj crystalline or	EPO; JPO;	
			polycrystalline or poly adj crystal or poly	DERWENT;	
			adj crystalline or polysilicon or large adj	IBM_TDB	
			grain) with (doping or dopant or doped or		
			implant or implanting or implantation or		
ĺ			implanted or diffusing or diffusion or		
ĺ			diffused) near4 (aluminum or al or nickel or		
			ni or titanium or ti or cobalt or co or		
			palladium or pd or transition adj metal)		

		*		
-	13	7 (tft or thin adj film adj transistor) and	USPAT;	2003/08/06 16:04
1	1	(single adj grain or single adj crystal or	US-PGPUB;	
		polycrystal or single adj crystalline or	EPO; JPO;	
		polycrystalline or poly adj crystal or poly	DERWENT;	
, ,	**	adj crystalline or polysilicon or large adj	IBM_TDB	
	-	grain) with (doping or dopant or doped or		
		implant or implanting or implantation or		·
		implanted or diffusing or diffusion or		
		diffused) near4 (aluminum or al or nickel or	ŀ	
		ni or titanium or ti or cobalt or co or	,	
`		palladium or pd or transition adj metal) and	-	
	-	(anneal or annealing or rta or annealed)		
-		5   ("5147826"   "5275851"   "6077731"	USPAT	2003/08/06 15:56
		"6084247"   "6162667").PN.		
}	47		USPAT;	2003/08/06 16:15
		(single adj grain or single adj crystal or	US-PGPUB;	-
		polycrystal or single adj crystalline or polycrystalline or poly adj crystal or poly	EPO; JPO;	
			DERWENT;	
ļ		adj crystalline or polysilicon or large adj grain or crystalline or crystallize or	IBM_TDB	
		crystallized or crystallization) near5		
		(catalyst or catalytic or nucleation) near		
		(aluminum or al or nickel or ni or titanium		
	1	or ti or cobalt or co or palladium or pd or		
		transition adj metal) and (anneal or		
1 5 " -		annealing or rta or annealed)		
· =	18		USPAT:	2003/08/06 16:08
		(single adj grain or single adj crystal or	US-PGPUB:	2003, 00, 00 20.00
		polycrystal or single adj crystalline or	EPO; JPO;	
		polycrystalline or poly adj crystal or poly	DERWENT;	
:		adj crystalline or polysilicon or large adj	IBM TDB	
		grain or crystalline or crystallize or	_	
1	, ,	crystallized or crystallization) near5		
		(catalyst or catalytic or nucleation) near4		
		(aluminum or al or nickel or ni or titanium		
		or ti or cobalt or co or palladium or pd or		
		transition adj metal) and (anneal or		-
		annealing or rta or annealed)) and (single		
		adj grain or single adj crystal or		
		polycrystal or single adj crystalline or		
-		polycrystalline or poly adj crystal or poly adj crystalline or polysilicon or large adj	,	
		grain or crystalline or crystallize or		
		crystallized or crystallization) near4		
		(source or drain or channel)		
_	3	(tft or thin adj film adj transistor) and	USPAT;	2003/08/06 16:16
[ ·		(single adj grain or single adj crystal or	US-PGPUB;	
1		polycrystal or single adj crystalline or	EPO; JPO;	
		polycrystalline or poly adj crystal or poly	DERWENT;	
		adj crystalline or polysilicon or large adj	IBM TDB	
		grain or crystalline or crystallize or	<del></del>	
		crystallized or crystallization) near5		
		(doped or doping or implanted or implanting		
		or dope or implant or diffuse or diffusion		
		or diffusing or diffused or implantation)		
		near3 (catalyst or catalytic or nucleation)		
	-	near4 (aluminum or al or nickel or ni or	,	
		titanium or ti or cobalt or co or palladium		
		or pd or transition adj metal) and (anneal		
		or annealing or rta or annealed)		
_		7 6162667.pn.	USPAT;	2003/08/07 10:35
	,		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	-	(15147926)   152750510   154011210	IBM_TDB	2002/02/25
	1	'	USPAT	2003/08/07.10:31
		"5534716"   "5543352"   "5550070"     "5580792"   "5585291"   "5612250"	,	
		"5643826"   "5654203").PN.		
<u> </u>				

			·	
-	75	(amorphous or polycrystalline) near3	USPAT;	2003/08/07 12:47
		(silicon or germanium or si or ge or sige)	US-PGPUB;	
		and (implant or implanting or implanted or	EPO; JPO;	-
		implantation) near2 (3d adj metal or	DERWENT;	
		transition adj metal or aluminum or nickel	IBM_TDB	-
		or ni or titanium or ti or cobalt or co or		
		palladium or pd) with (crystallization or		
		crystallize or crystallized or crystallizing		
		or single near2 crystal or single near2		
	1	grain)		2002/20/20
	11	("4571486"   "4772927"   "4986213"	USPAT	2003/08/07 12:14
		"5147826"   "5156994"   "5236850"		
		"5252502"   "5275851"   "5278093"		
	21	"5328861"   "5352291").PN.   ("4420870"   "4514253"   "4727044"	11003 0	0000/00/00
_	21		USPAT	2003/08/07 12:44
		1 !		
		"4772927"   "4912061"   "5142344"     "5147826"   "5229625"   "5275851"		
1	17.			
		"5563426"   "5563440"   "5569936"     "5576556"   "5592008"   "5608232").PN.	1.	
1_	20	(amorphous or polycrystalline) near3	IICDATE-	2003/08/07 14:19
	20	(silicon or germanium or si or ge or sige)	USPAT;	2003/06/0/ 14:19
		and (implant or implanting or implanted or	US-PGPUB; EPO; JPO;	
		implantation or doping or doped or dope or	DERWENT;	
		diffusing or diffusion or diffused) near2	IBM TDB	
		(3d adj metal or transition adj metal or	TBM_TB	
		aluminum or nickel or ni or titanium or ti		
		or cobalt or co or palladium or pd) with		
		(crystallization or crystallize or		
		crystallized or crystallizing or single		1
		near2 crystal or single near2 grain) and		
ĺ		(nucleus or nucleation) near8 (radius or		
		separation or distance or spaced or		
		separated or separate or distanced or		
		interval or density)		
_	8	(amorphous or polycrystalline) near3	USPAT;	2003/08/07 13:19
	, -	(silicon or germanium or si or ge or sige)	US-PGPUB;	2003,00,07
		and (implant or implanting or implanted or	EPO; JPO;	{
		implantation or doping or doped or dope or	DERWENT;	
		diffusing or diffusion or diffused) near2	IBM TDB	
		(3d adj metal or transition adj metal or		
		aluminum or nickel or ni or titanium or ti		
		or cobalt or co or palladium or pd) with		
		(crystallization or crystallize or		
		crystallized or crystallizing or single		-
		near2 crystal or single near2 grain) and		,
1		(nucleus or nucleation or catalyst or metal		·
		or catalytic or crystal or crystallization)		
		near3 (site or center or origin or location)		·
		near8 (radius or separation or distance or		
		spaced or separated or separate or distanced		
	,	or interval or density)		
-	25	(amorphous or polycrystalline) near3	USPAT;	2003/08/07 14:05
		(silicon or germanium or si or ge or sige)	US-PGPUB;	
1		and (nucleus or nucleation) near5 (aluminum	EPO; JPO;	
		or nickel or ni or cobalt or co or palladium	DERWENT;	
		or pd or titanium or ti or 3d near metal or	IBM_TDB	
1		transition near metal) near6 (radius or	_	
		separation or distance or spaced or		_
		separated or separate or distanced or		·
		interval or density)		
-	109	257/70.ccls.	USPAT;	2003/08/07 14:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		Manufacture Company of the Company o	IBM_TDB	<u> </u>
			<del></del>	

-	T	49	(amorphous or polycrystalline) near3	USPAT;	2003/08/07 14:35
			(silicon or germanium or si or ge or sige)	US-PGPUB;	
			and (implant or implanting or implanted or	EPO; JPO;	
			implantation or doping or doped or dope or	DERWENT;	
	1		diffusing or diffusion or diffused) near2	IBM_TDB	
•			(3d adj metal or transition adj metal or	_	
			aluminum or nickel or ni or titanium or ti		
			or cobalt or co or palladium or pd) with		
	1		(crystallization or crystallize or		
			crystallized or crystallizing or single		
			near2 crystal or single near2 grain) and		
			(grain) near3 (radius or separation or		
			distance or spaced or separated or separate	l .	
		<i>-</i> -	or distanced or interval or density)		
_		65	(amorphous or polycrystalline) near3	USPAT;	2003/08/07 15:47
			(silicon or germanium or si or ge or sige)	US-PGPUB;	
			and (implant or implanting or implanted or	EPO; JPO;	
			implantation or doping or doped or dope or	DERWENT;	
			diffusing or diffusion or diffused) near2	IBM_TDB	
			(3d adj metal or transition adj metal or		
			aluminum or nickel or ni or titanium or ti		
			or cobalt or co or palladium or pd) with		
			(crystallization or crystallize or		
			crystallized or crystallizing or single		
			near2 crystal or single near2 grain) and		
			(grain) near3 (distance or size or		
			separation)		
_		348	(tft or thin adj film adj transistor) and	USPAT;	2003/08/07 15:48
		310	(single adj (grain or crystal)) near4	US-PGPUB;	2003/00/07 13:40
			(channel or source or drain)	EPO; JPO;	
			(channel of source of drain)	DERWENT;	,
				1 .	· ·
		16	(tett on thin odd film odd twongiston) and	IBM_TDB	2002/02/03 16 20
-	1	10	(tft or thin adj film adj transistor) and	USPAT;	2003/08/07 16:20
			(single adj (grain or crystal)) near4	US-PGPUB;	
			(channel or source or drain) with (metal or	EPO; JPO;	
			aluminum or titanium or ti or nickel or ni	DERWENT;	
	1		or cobalt or co or palladium or pd)	IBM_TDB	
- "		235	438/162.ccls.	USPAT;	2003/08/07 16:21
				US-PGPUB;	
	ľ			EPO; JPO;	
			· ·	DERWENT;	
•				IBM_TDB	
=		99	438/162.ccls. and (crystallization or	USPAT;	2003/08/07 16:38
			crystallize or recrystallization or	US-PGPUB;	
			recrystallize or crystallized or	EPO; JPO;	
	1		crystallizing or recrystallized or	DERWENT;	
			recrystallizing or polycrystalline or	IBM_TDB	
			amorphous) near8 (catalyst or metal or		
			aluminum or titanium or cobalt or palladium		
			or nickel)	1	
_	1.	63		HCDAM	2007/00/07 15:33
-		62	438/162.ccls. and (crystallization or	USPAT;	2003/08/07 16:43
	,		crystallize or recrystallization or	US-PGPUB;	
			recrystallize or crystallized or	EPO; JPO;	· ·
	-		crystallizing or recrystallized or	DERWENT;	
			recrystallizing or polycrystalline or	IBM_TDB	
	1		amorphous) near8 (nickel)		